



# BUK9215-55A

## N-channel TrenchMOS logic level FET

7 April 2014

Product data sheet

### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

### 4. Quick reference data

Table 1. Quick reference data

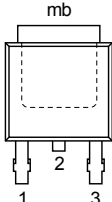
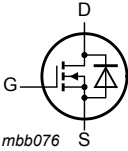
| Symbol                  | Parameter                        | Conditions                                                                                                              |                     | Min | Typ | Max  | Unit |
|-------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------|---------------------|-----|-----|------|------|
| V <sub>DS</sub>         | drain-source voltage             | T <sub>J</sub> ≥ 25 °C; T <sub>J</sub> ≤ 175 °C                                                                         |                     | -   | -   | 55   | V    |
| I <sub>D</sub>          | drain current                    | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                         | <a href="#">[1]</a> | -   | -   | 62   | A    |
| P <sub>tot</sub>        | total power dissipation          | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                         |                     | -   | -   | 115  | W    |
| Static characteristics  |                                  |                                                                                                                         |                     |     |     |      |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C                                                   |                     | -   | 11  | 13.6 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C                                                  |                     | -   | -   | 16.6 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a> |                     | -   | 13  | 15   | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                         |                     |     |     |      |      |
| Q <sub>GD</sub>         | gate-drain charge                | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 44 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 9</a>    |                     | -   | 20  | -    | nC   |

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                     | Min | Typ | Max | Unit |
|-----------------------------|----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                |     |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 62\text{ A}$ ; $V_{sup} \leq 55\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 5\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped | -   | -   | 211 | mJ   |

[1] Current is limited by power dissipation chip rating.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                            | Graphic symbol                                                                                           |
|-----|--------|-----------------------------------|---------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------|
| 1   | G      | gate                              |  <p><b>DPAK (SOT428)</b></p> |  <p><i>mbb076</i></p> |
| 2   | D      | drain                             |                                                                                                               |                                                                                                          |
| 3   | S      | source                            |                                                                                                               |                                                                                                          |
| mb  | D      | mounting base; connected to drain |                                                                                                               |                                                                                                          |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |                                                                                 |         |
|-------------|---------|---------------------------------------------------------------------------------|---------|
|             | Name    | Description                                                                     | Version |
| BUK9215-55A | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

## 7. Limiting values

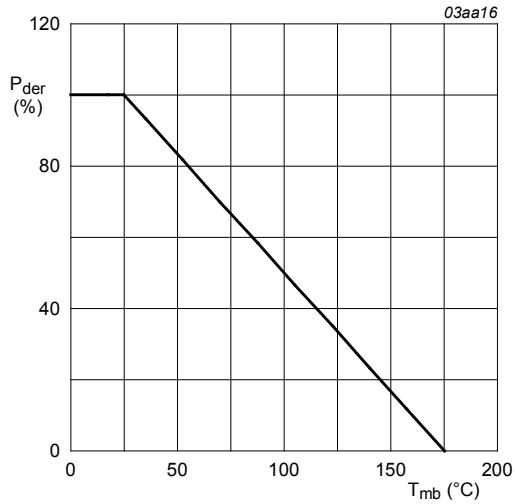
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol                      | Parameter                                    | Conditions                                                                                                                                        |                     | Min | Max | Unit |
|-----------------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|---------------------|-----|-----|------|
| $V_{DS}$                    | drain-source voltage                         | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                                                                                |                     | -   | 55  | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $R_{GS} = 20\text{ k}\Omega$                                                                                                                      |                     | -   | 55  | V    |
| $V_{GS}$                    | gate-source voltage                          |                                                                                                                                                   |                     | -15 | 15  | V    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                                                  |                     | -   | 115 | W    |
| $I_D$                       | drain current                                | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                                                 | <a href="#">[1]</a> | -   | 62  | A    |
|                             |                                              |                                                                                                                                                   | <a href="#">[2]</a> | -   | 55  | A    |
|                             |                                              | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a>                                                                         | <a href="#">[1]</a> | -   | 44  | A    |
| $I_{DM}$                    | peak drain current                           | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 3</a>                                                       |                     | -   | 248 | A    |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                   |                     | -55 | 175 | °C   |
| $T_j$                       | junction temperature                         |                                                                                                                                                   |                     | -55 | 175 | °C   |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                   |                     |     |     |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                           | <a href="#">[2]</a> | -   | 55  | A    |
|                             |                                              |                                                                                                                                                   | <a href="#">[1]</a> | -   | 62  | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                |                     | -   | 248 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                   |                     |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 62\text{ A}$ ; $V_{sup} \leq 55\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 5\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped |                     | -   | 211 | mJ   |

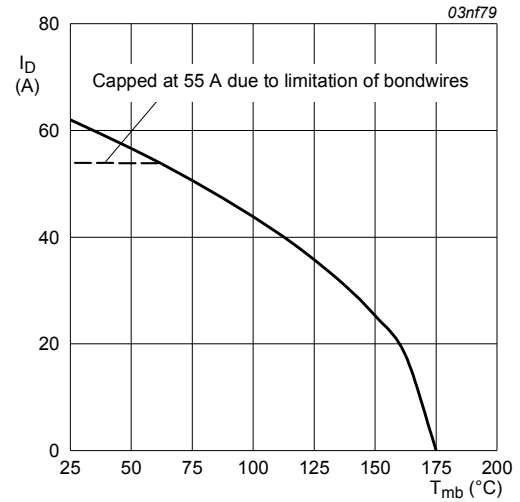
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by bond wires.



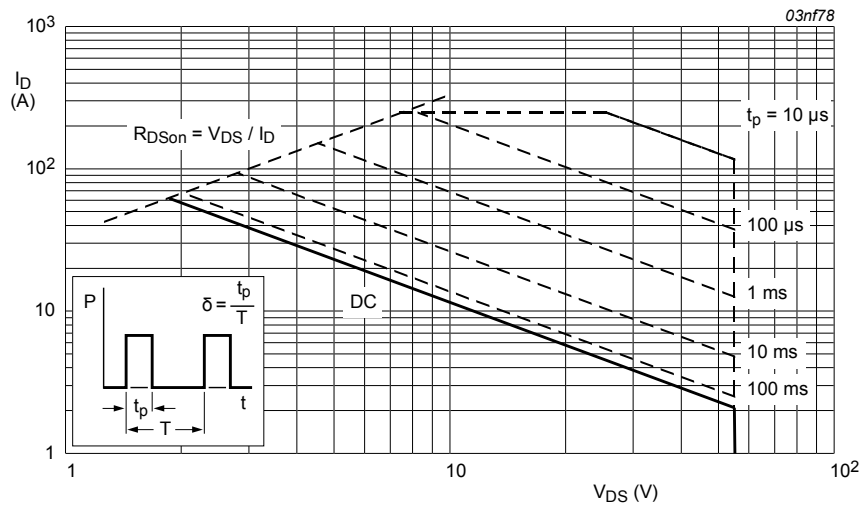
**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$



**Fig. 2. Continuous drain current as a function of mounting base temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$



**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

$$T_{mb} = 25^{\circ}\text{C}; I_{DM} \text{ is single pulse}$$

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions             |  | Min | Typ  | Max | Unit |
|----------------|---------------------------------------------------|------------------------|--|-----|------|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 4</a> |  | -   | -    | 1.3 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       |                        |  | -   | 71.4 | -   | K/W  |

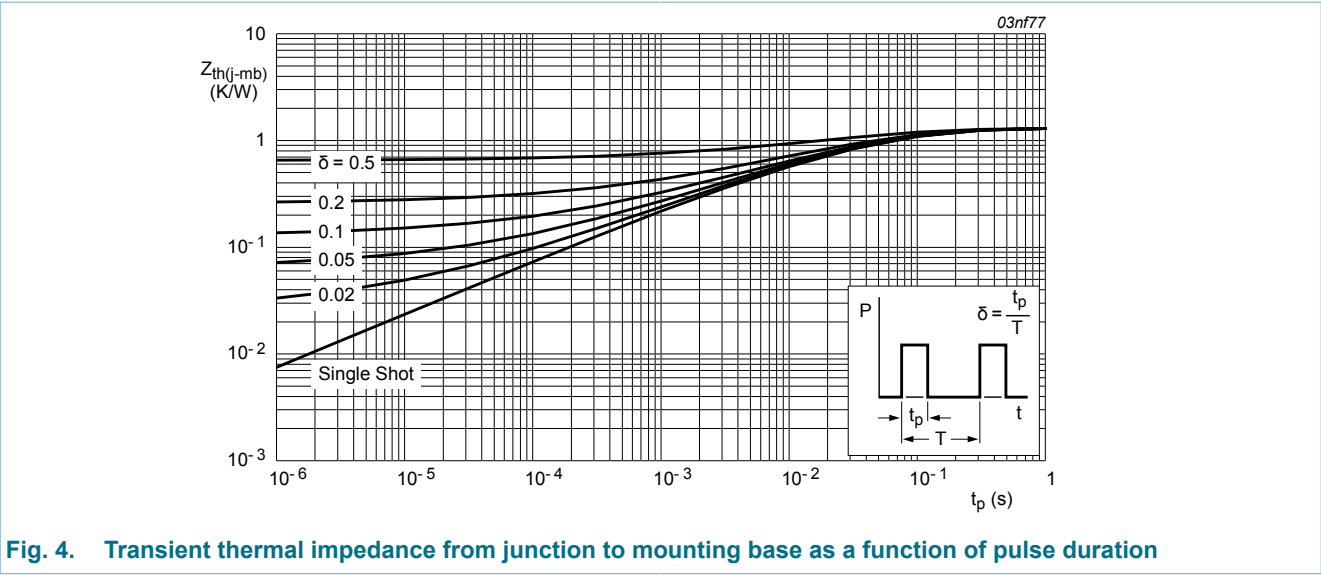


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                |  | Min | Typ  | Max  | Unit |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics  |                                  |                                                                                                                           |  |     |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                   |  | 55  | -    | -    | V    |
|                         |                                  | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                  |  | 50  | -    | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 10</a>               |  | -   | -    | 2.3  | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <a href="#">Fig. 10</a>               |  | 0.5 | -    | -    | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                |  | 1   | 1.5  | 2    | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | 0.05 | 10   | μA   |
|                         |                                  | V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                                    |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | 2    | 100  | nA   |
|                         |                                  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                    |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                                                     |  | -   | 11   | 13.6 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                                                    |  | -   | -    | 16.6 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>  |  | -   | -    | 30   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>   |  | -   | 13   | 15   | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                           |  |     |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>      |  | -   | 48   | -    | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                           |  | -   | 6    | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                           |  | -   | 20   | -    | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a>                 |  | -   | 2190 | 2916 | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                           |  | -   | 380  | 450  | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                           |  | -   | 250  | 344  | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C |  | -   | 19   | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                           |  | -   | 161  | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                           |  | -   | 138  | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                           |  | -   | 165  | -    | ns   |
| L <sub>D</sub>          | internal drain inductance        | measured from drain to centre of die                                                                                      |  | -   | 2.5  | -    | nH   |

| Symbol             | Parameter                  | Conditions                                                                    | Min | Typ  | Max | Unit |
|--------------------|----------------------------|-------------------------------------------------------------------------------|-----|------|-----|------|
| L <sub>S</sub>     | internal source inductance | measured from source lead to source bond pad                                  | -   | 7.5  | -   | nH   |
| Source-drain diode |                            |                                                                               |     |      |     |      |
| V <sub>SD</sub>    | source-drain voltage       | I <sub>S</sub> = 20 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C; Fig. 14 | -   | 0.85 | 1.2 | V    |
| t <sub>rr</sub>    | reverse recovery time      | I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;                       | -   | 51   | -   | ns   |
| Q <sub>r</sub>     | recovered charge           | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>J</sub> = 25 °C       | -   | 102  | -   | nC   |

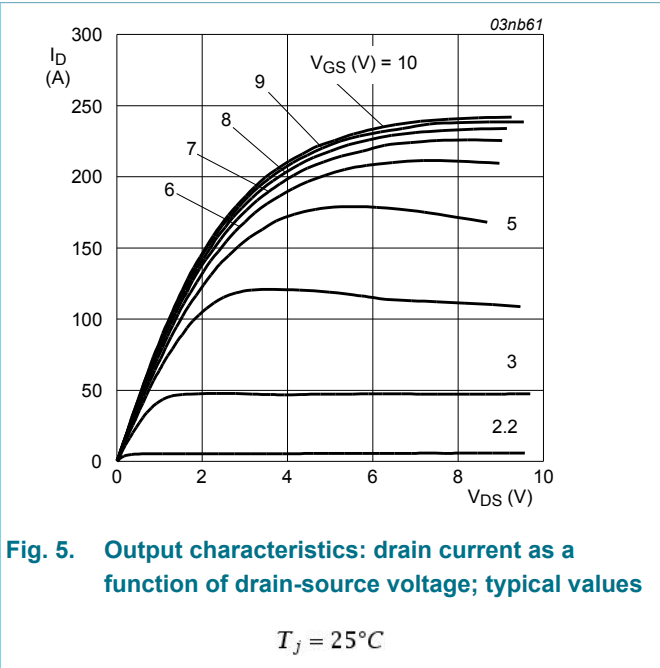


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

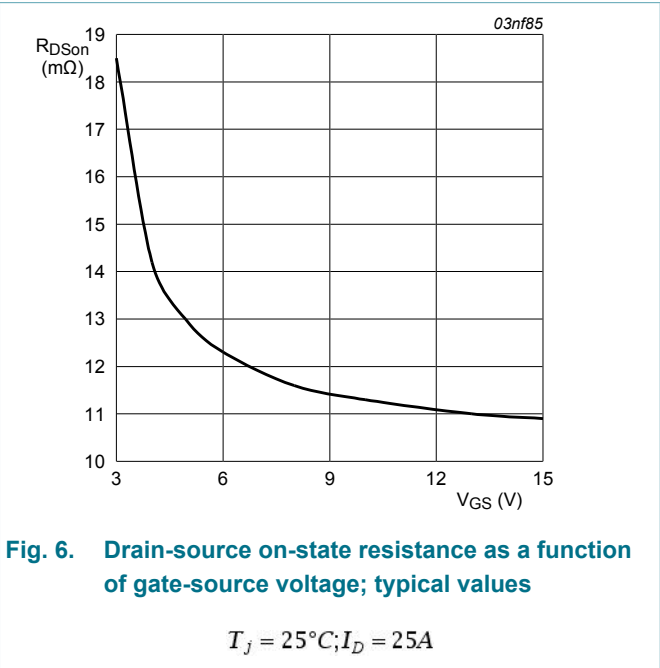


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

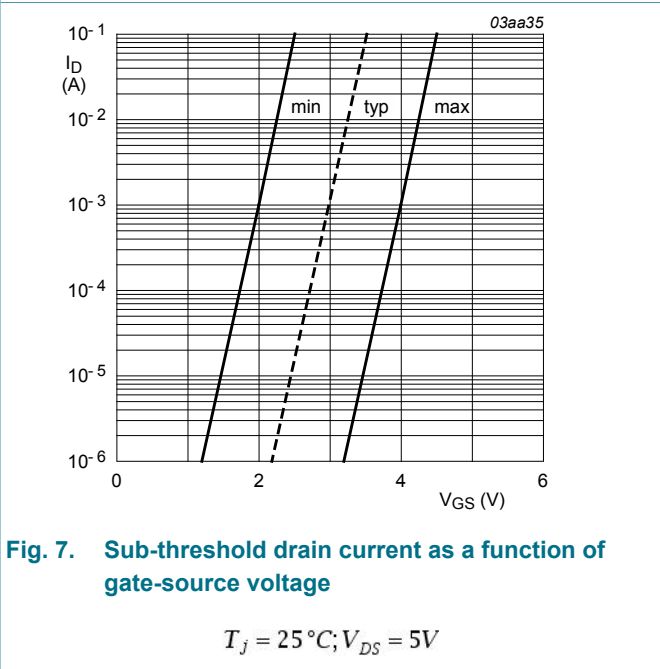


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

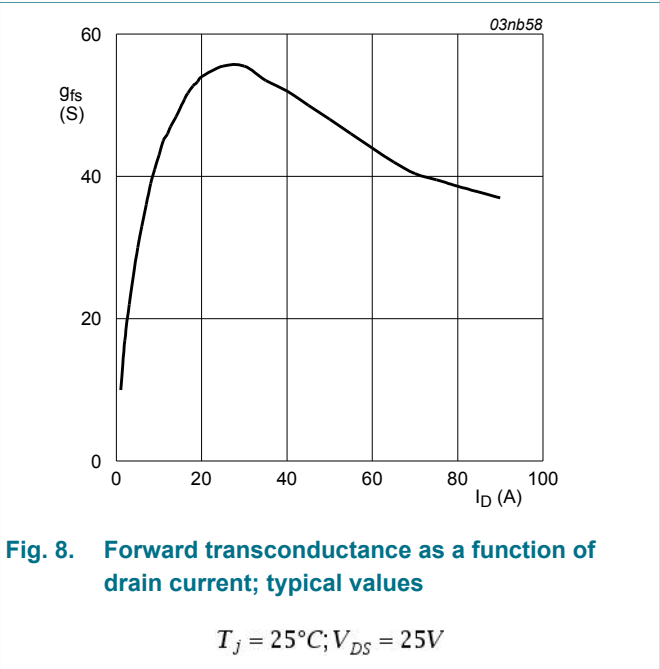


Fig. 8. Forward transconductance as a function of drain current; typical values

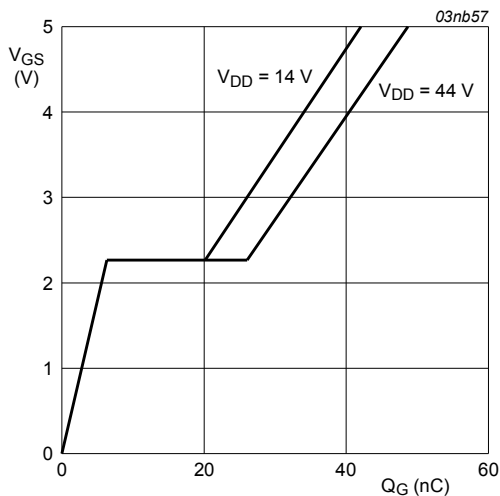


Fig. 9. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 25\text{ A}$$

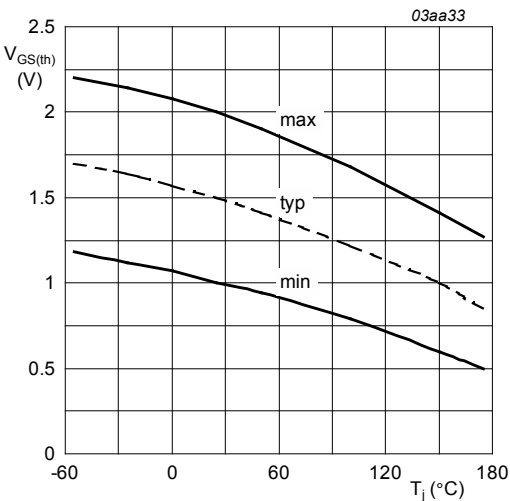


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

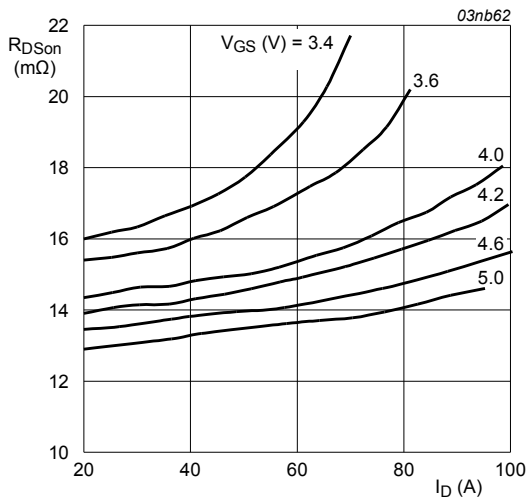


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}\text{C}$$

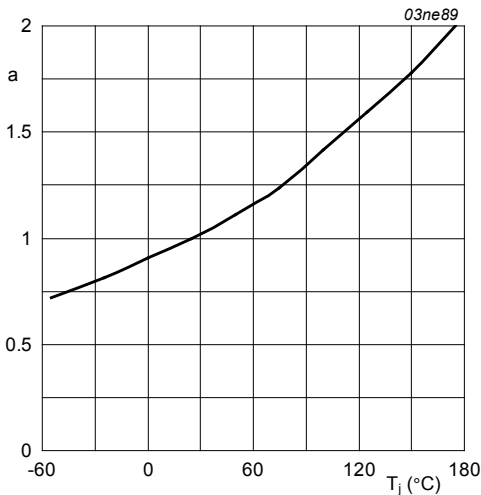


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$



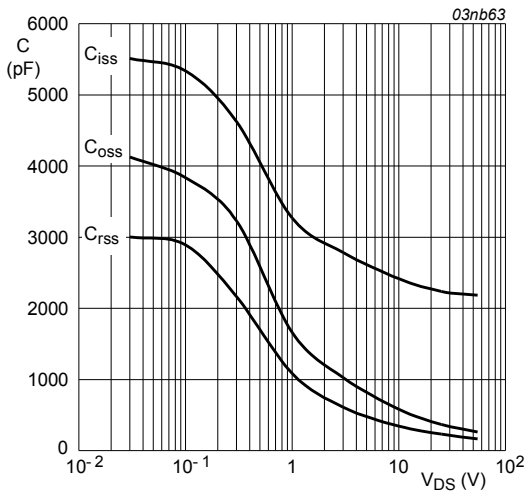


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

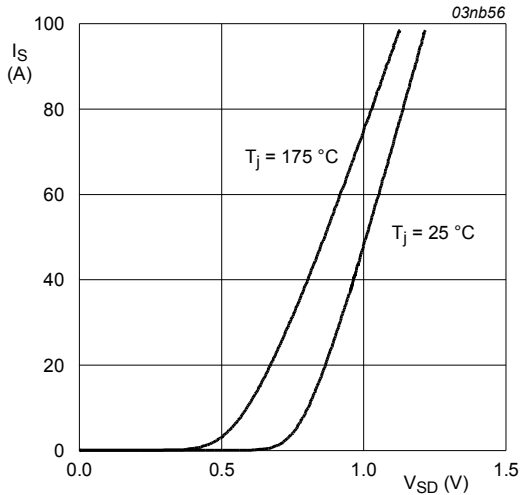


Fig. 14. Reverse diode current; typical value

$$V_{GS} = 0V$$

10. Package outline

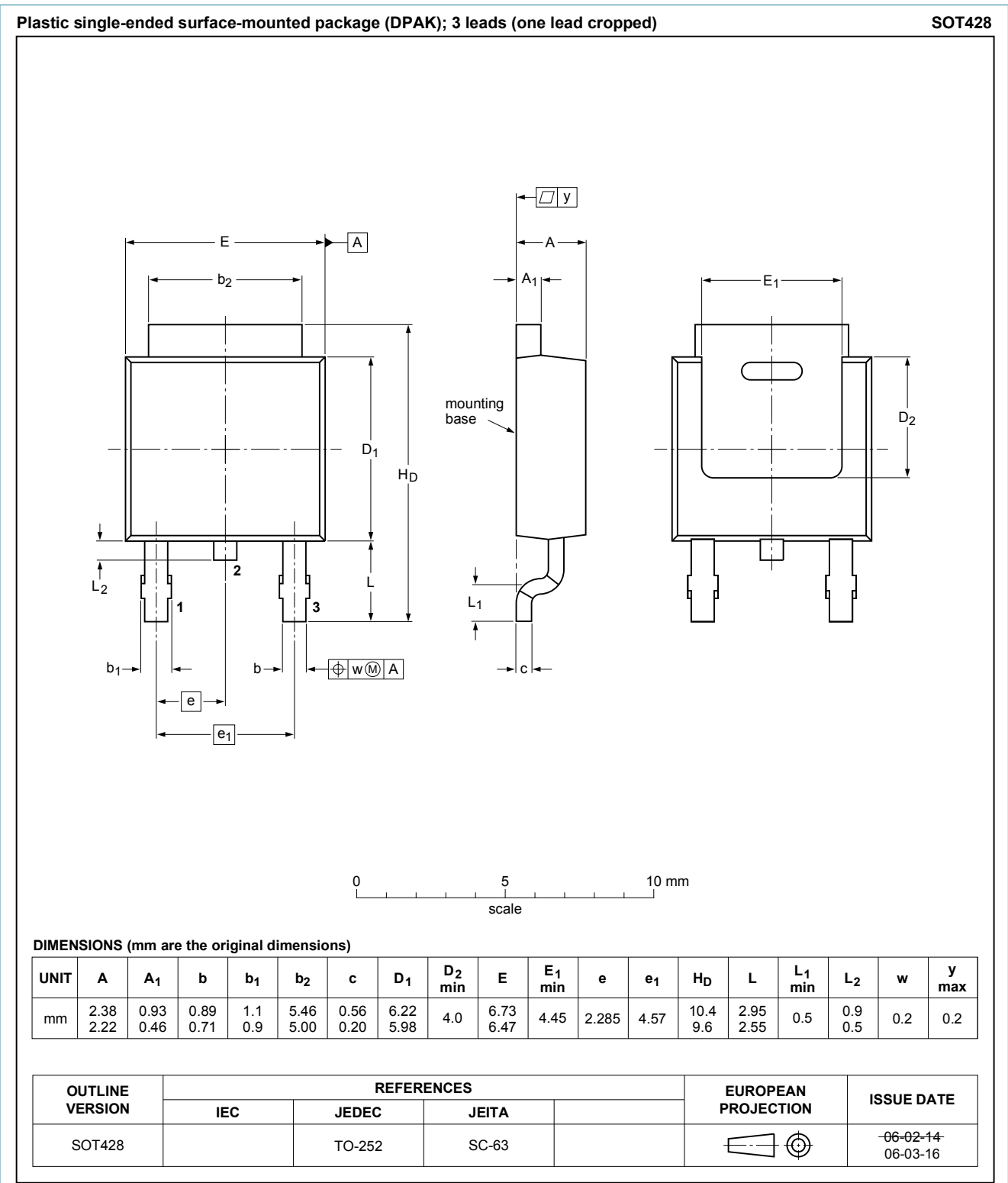


Fig. 15. Package outline DPAK (SOT428)

## 11. Legal information

### 11.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## Данный компонент на территории Российской Федерации

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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